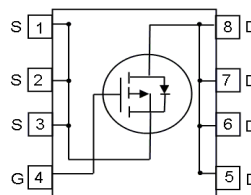
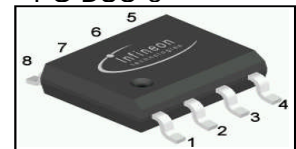


**OptiMOS™ 3 P3-Power-Transistor**
**Features**

- single P-Channel in SO8
- Qualified according JEDEC<sup>1)</sup> for target applications
- 150°C operating temperature
- $V_{GS}=25\text{ V}$ , specially suited for notebook applications
- Pb-free plating; RoHS compliant
- applications: battery management, load switching
- Halogen-free according to IEC61249-2-21


**Halogen-Free**
**Product Summary**

$V_{DS}$		-30	V
$R_{DS(on),max}$	$V_{GS}=-10\text{ V}$	8.0	mΩ
	$V_{GS}=-6\text{ V}$	11.4	
$I_D$		-14.8	A


**PG-DSO-8**


Type	Package	Marking	Lead free	Halogen free	Packing
BSO080P03NS3 G	PG-DSO-8	080P3NS	Yes	Yes	non dry

**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value		Unit
			10 secs	steady state	
Continuous drain current <sup>1)</sup>	$I_D$	$V_{GS}=-10\text{ V}, T_A=25\text{ °C}$	-14.8	-12	A
		$V_{GS}=-10\text{ V}, T_A=70\text{ °C}$	-11.8	-9.4	
		$V_{GS}=-6\text{ V}, T_A=25\text{ °C}$	-12.4	-9.8	
		$V_{GS}=-6\text{ V}, T_A=70\text{ °C}$	-9.9	-7.8	
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	$T_A=25\text{ °C}$	-48		
Avalanche energy, single pulse	$E_{AS}$	$I_D=-14.8\text{ A}, R_{GS}=25\text{ Ω}$	149		mJ
Gate source voltage	$V_{GS}$		±25		V
Power dissipation <sup>1)</sup>	$P_{tot}$	$T_A=25\text{ °C}$	2.5	1.6	W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 150		°C
ESD class		JESD22-A114 HBM	1C (1 kV - 2 kV)		
Soldering temperature			260		°C
IEC climatic category; DIN IEC 68-1			55/150/56		

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - soldering point	$R_{thJS}$		-	-	35	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	minimal footprint, $t_p \leq 10$ s	-	-	110	
		minimal footprint, steady state	-	-	150	
		6 cm <sup>2</sup> cooling area <sup>1)</sup> , $t_p \leq 10$ s	-	-	50	
		6 cm <sup>2</sup> cooling area <sup>1)</sup> , steady state	-	-	80	

**Electrical characteristics, at  $T_j=25$  °C, unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0$ V, $I_D=-0.25$ mA	-30	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=-150$ $\mu$ A	-3.1	-2.5	-1.9	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=-30$ V, $V_{GS}=0$ V, $T_j=25$ °C	-	-	-1	$\mu$ A
		$V_{DS}=-30$ V, $V_{GS}=0$ V, $T_j=125$ °C	-	-	-100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=-25$ V, $V_{DS}=0$ V	-	-	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=-6$ V, $I_D=-12.4$ A	-	8.1	11.0	m $\Omega$
		$V_{GS}=-10$ V, $I_D=-14.8$ A	-	6.7	8.0	
Gate resistance	$R_G$		-	5.9	-	$\Omega$
Transconductance	$g_{fs}$	$ V_{DS}  > 2 I_D  R_{DS(on)max}$ , $I_D=-14.8$ A	22	44	-	S

<sup>1)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu$ m thick) copper area for drain connection. PCB is vertical in still air.

<sup>2)</sup> See figure 3 for more detailed information

<sup>3)</sup> See figure 13 for more detailed information

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=-15\text{ V}, f=1\text{ MHz}$	-	4500	6750	pF
Output capacitance	$C_{oss}$		-	2100	3150	
Reverse transfer capacitance	$C_{rss}$		-	150	225	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-15\text{ V}, V_{GS}=-10\text{ V}, I_D=-14.8\text{ A}, R_G=1.6\ \Omega$	-	16	24	ns
Rise time	$t_r$		-	47	70	
Turn-off delay time	$t_{d(off)}$		-	64	96	
Fall time	$t_f$		-	19	28.5	

**Gate Charge Characteristics<sup>4)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=-15\text{ V}, I_D=-14.8\text{ A}, V_{GS}=0\text{ to }-10\text{ V}$	-	18	23	nC
Gate charge at threshold	$Q_{g(th)}$		-	7	10	
Gate to drain charge	$Q_{gd}$		-	8	11	
Switching charge	$Q_{sw}$		-	18	25	
Gate charge total	$Q_g$		-	61	81	
Gate plateau voltage	$V_{plateau}$		-	3.9	-	V
Output charge	$Q_{oss}$	$V_{DD}=-15\text{ V}, V_{GS}=0\text{ V}$	-	49	65	nC

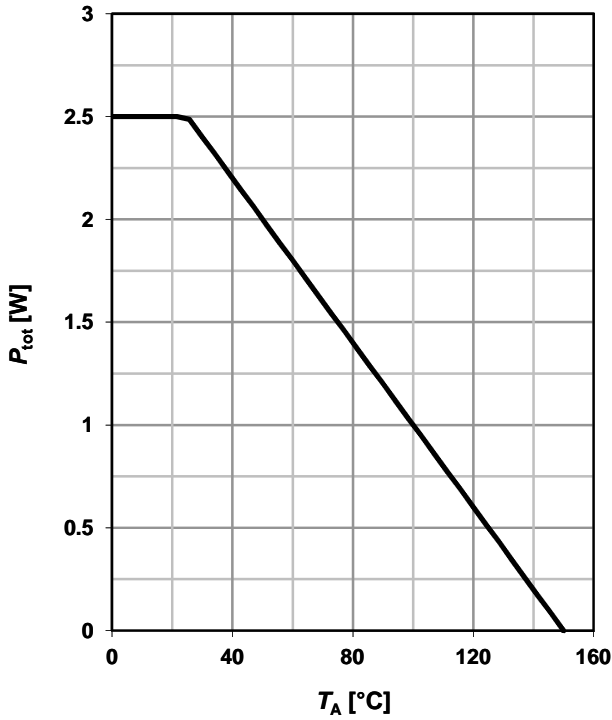
**Reverse Diode**

Diode continuous forward current	$I_S$	$T_A=25\text{ }^\circ\text{C}$	-	-	3.4	A
Diode pulse current	$I_{S,pulse}$		-	-	48	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=-14.8\text{ A}, T_j=25\text{ }^\circ\text{C}$	-	-	-1.1	V
Reverse recovery charge	$Q_{rr}$	$V_R=-15\text{ V}, I_F=I_S, di_F/dt=400\text{ A}/\mu\text{s}$	-	48	-	nC
Reverse recovery time	$t_{rr}$		-	49	-	ns

<sup>4)</sup> See figure 16 for gate charge parameter definition

**1 Power dissipation**

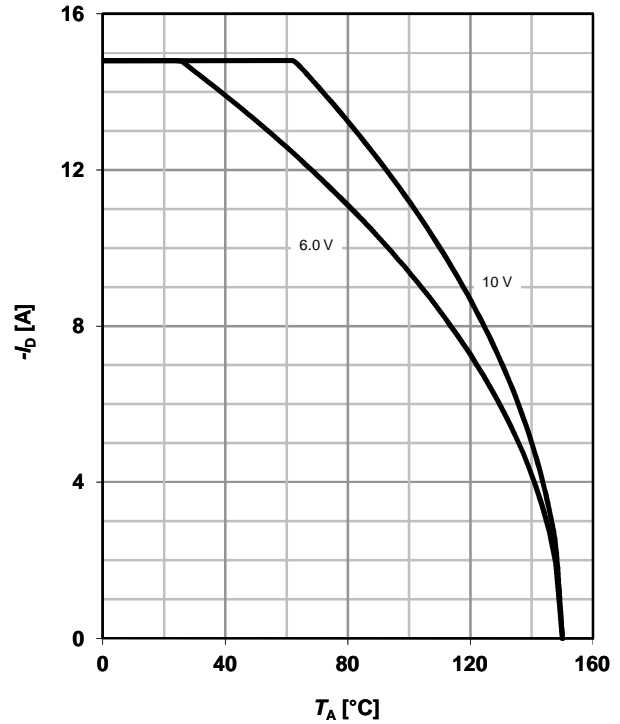
$P_{tot}=f(T_A); t_p \leq 10 \text{ s}$



**2 Drain current**

$I_D=f(T_A); t_p \leq 10 \text{ s}$

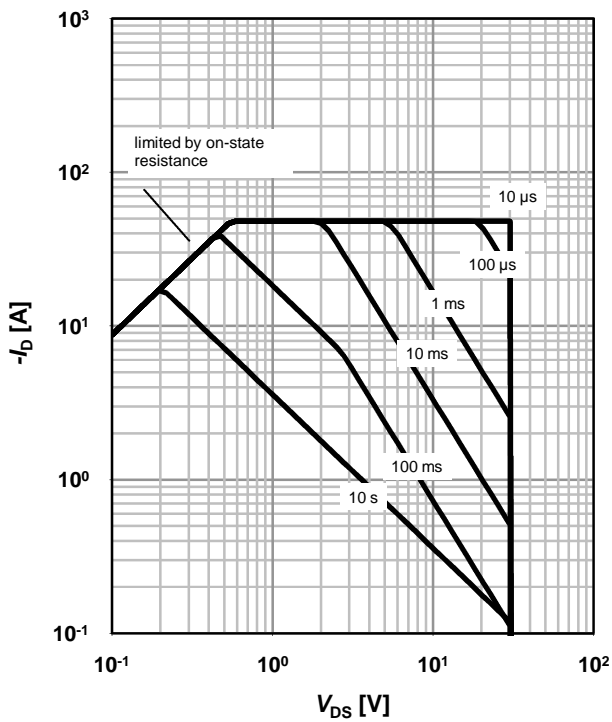
parameter:  $V_{GS}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_A=25 \text{ °C}^2; D=0$

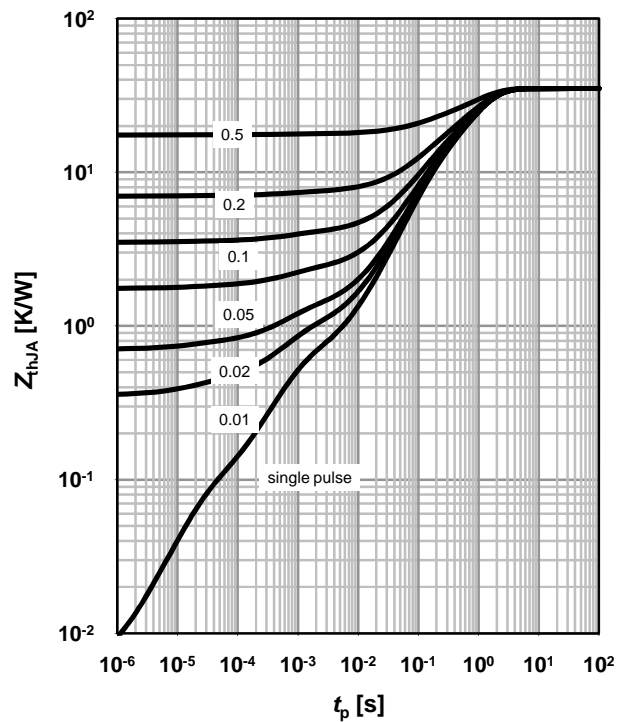
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJA}=f(t_p)^2$

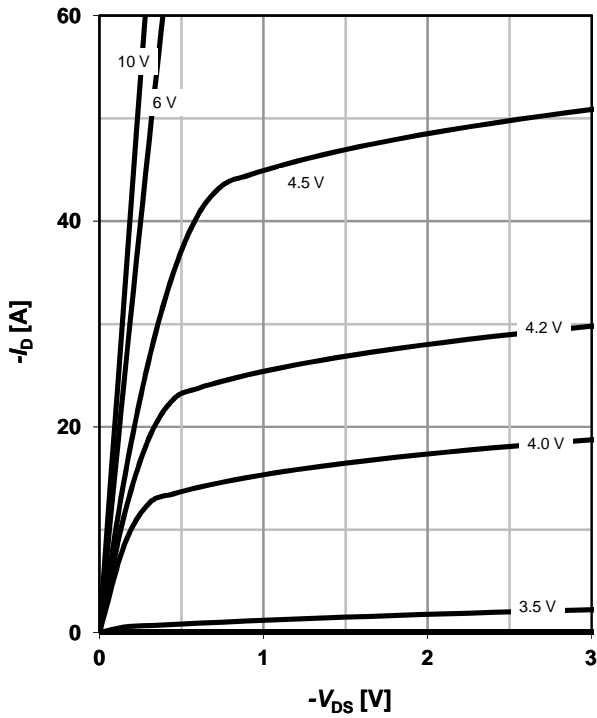
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ °C}$

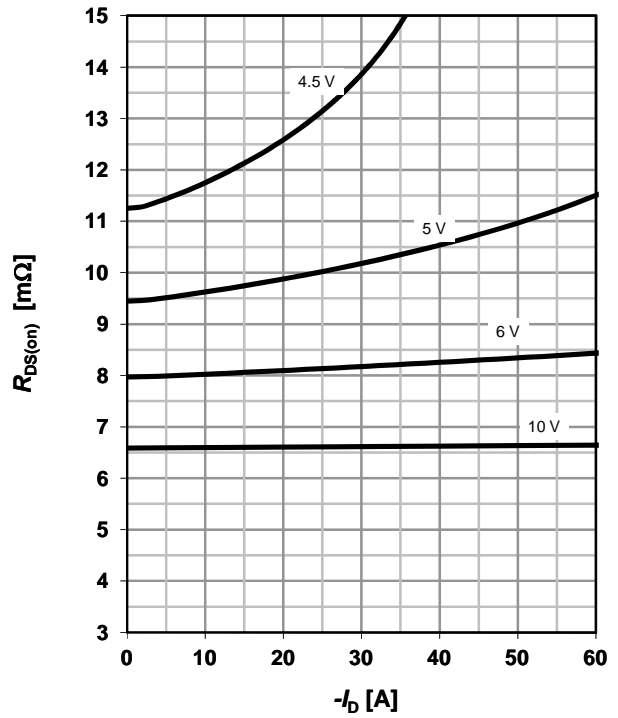
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$

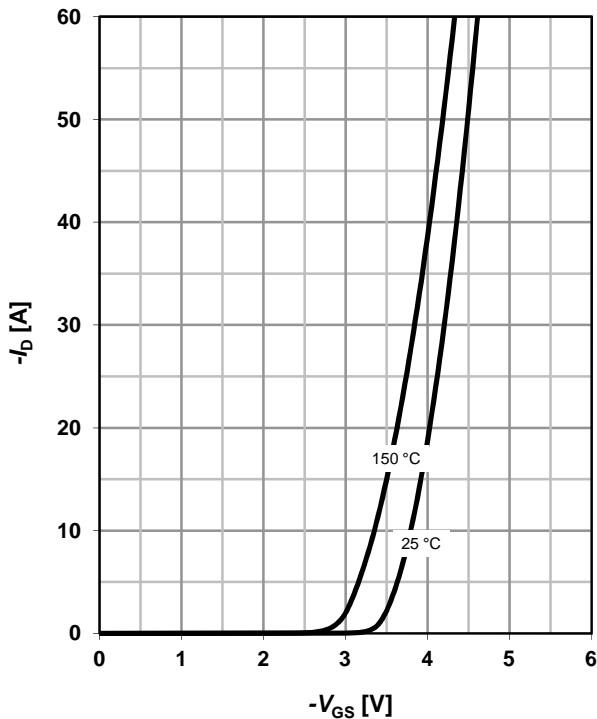
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

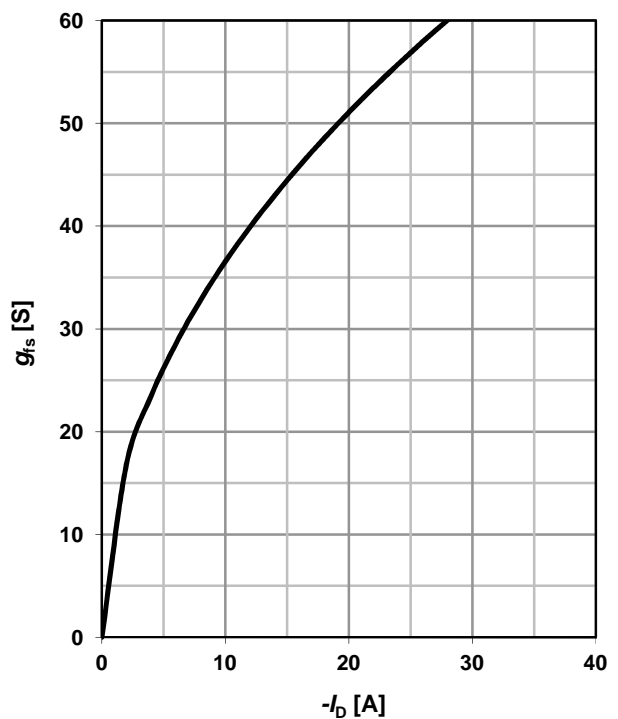
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



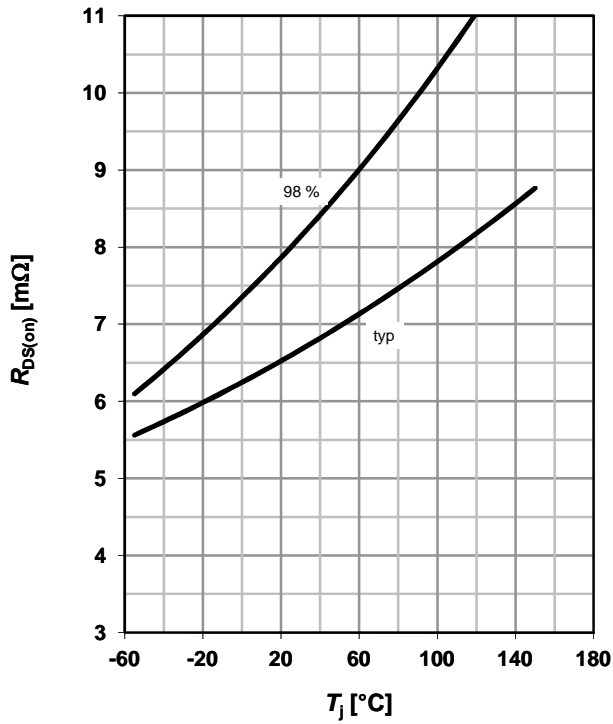
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ °C}$



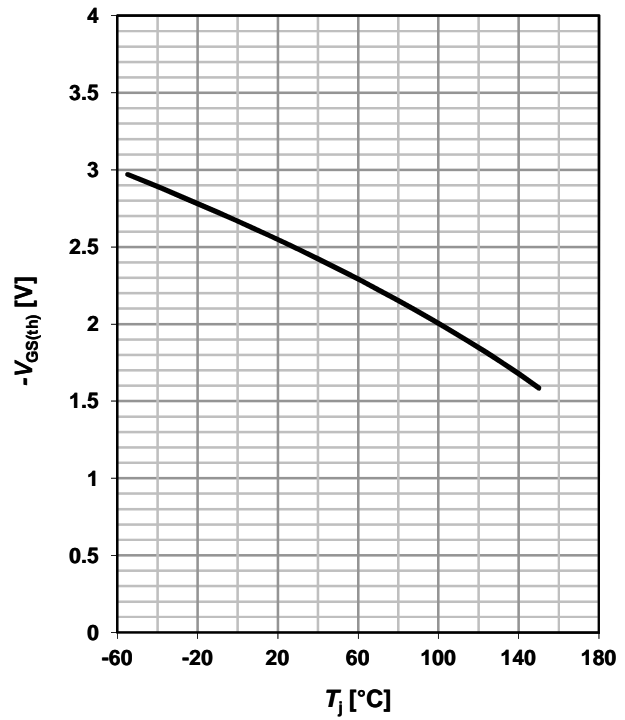
**9 Drain-source on-state resistance**

$R_{DS(on)}=f(T_j); I_D=-14.8\text{ A}; V_{GS}=-10\text{ V}$



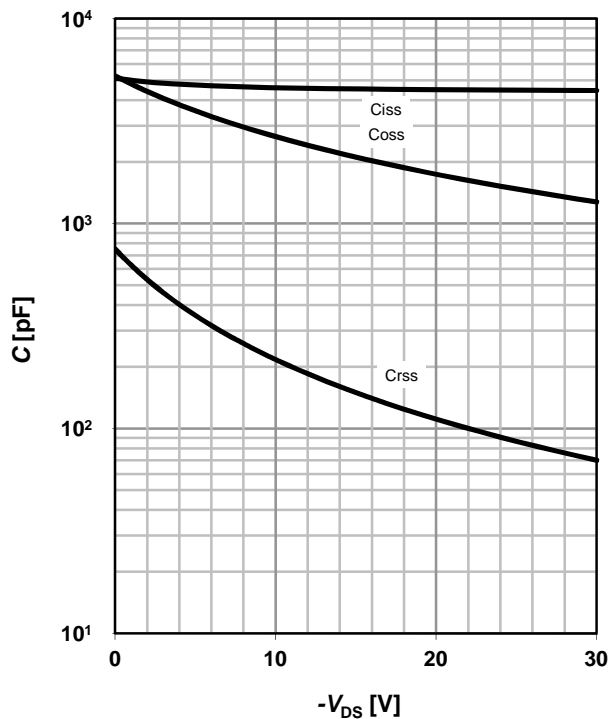
**10 Typ. gate threshold voltage**

$V_{GS(th)}=f(T_j); V_{GS}=V_{DS}; I_D=-150\mu\text{A}$



**11 Typ. capacitances**

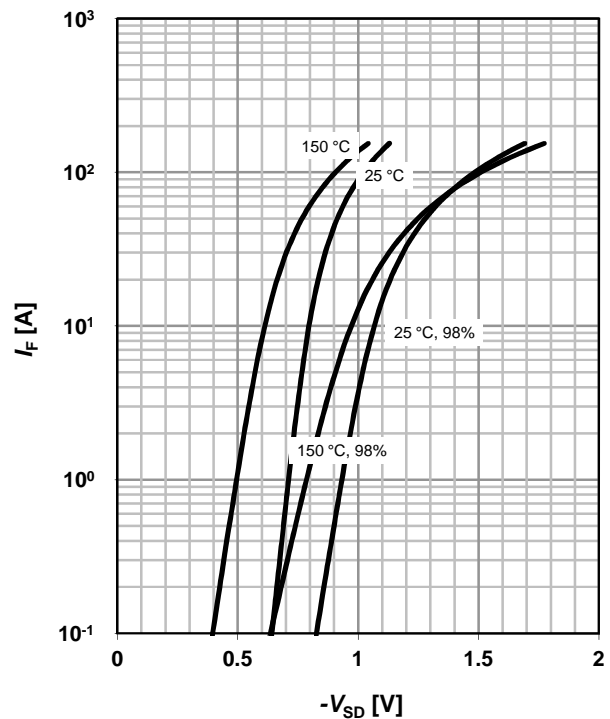
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F=f(V_{SD})$

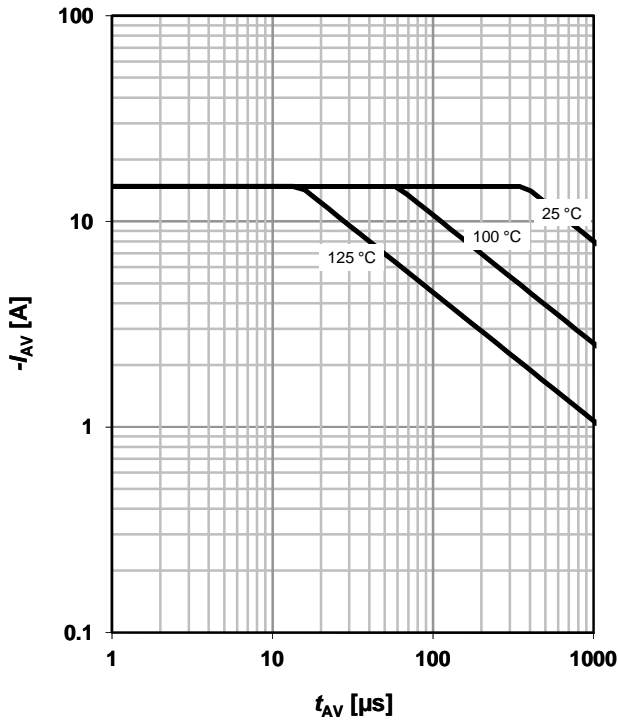
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

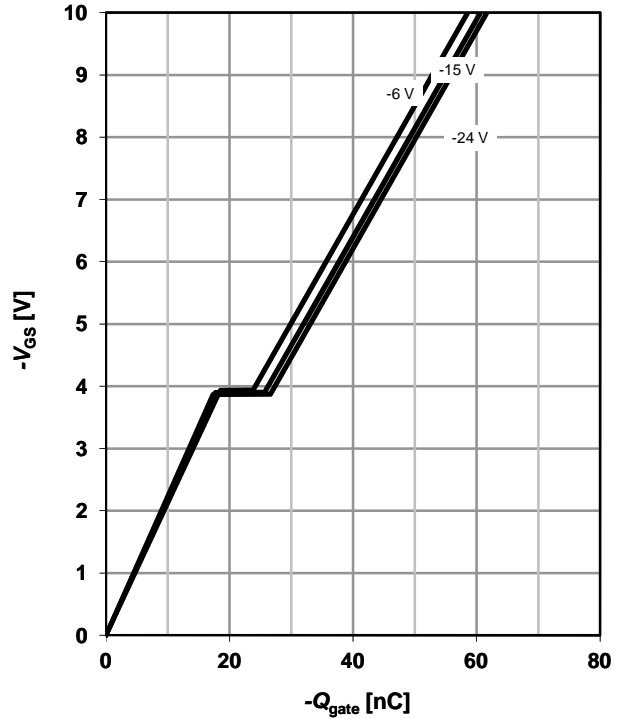
parameter:  $T_{j(\text{start})}$



**14 Typ. gate charge**

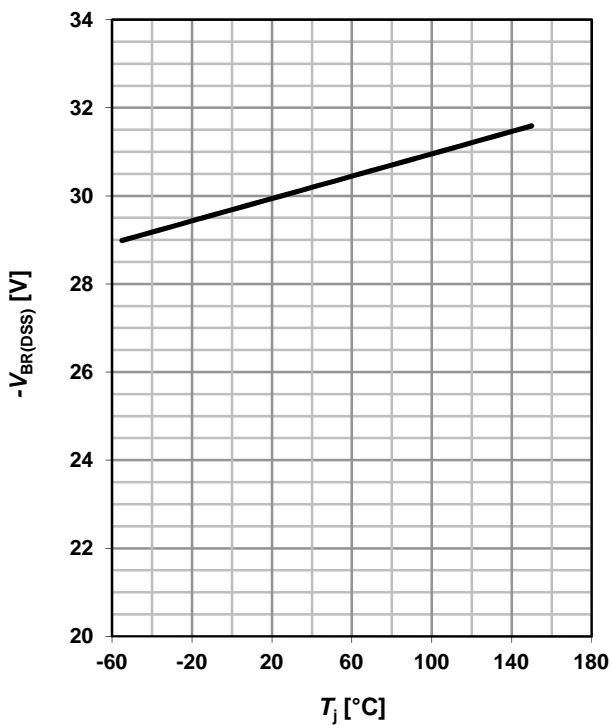
$V_{GS}=f(Q_{\text{gate}}); I_D=-14.8 \text{ A pulsed}$

parameter:  $V_{DD}$

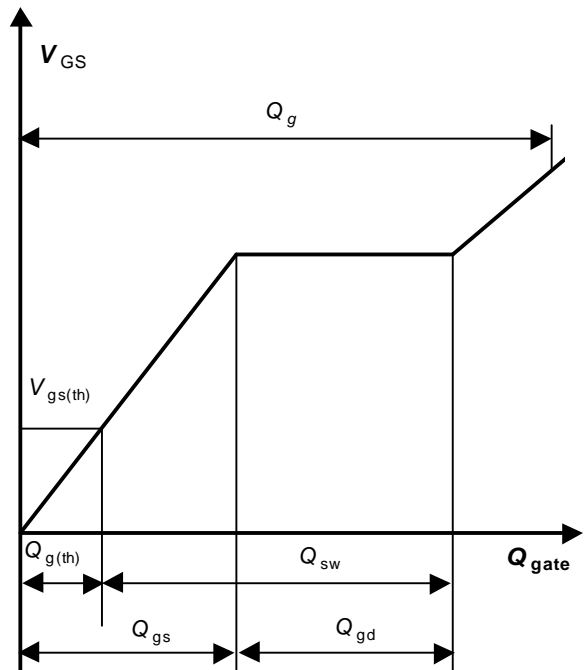


**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

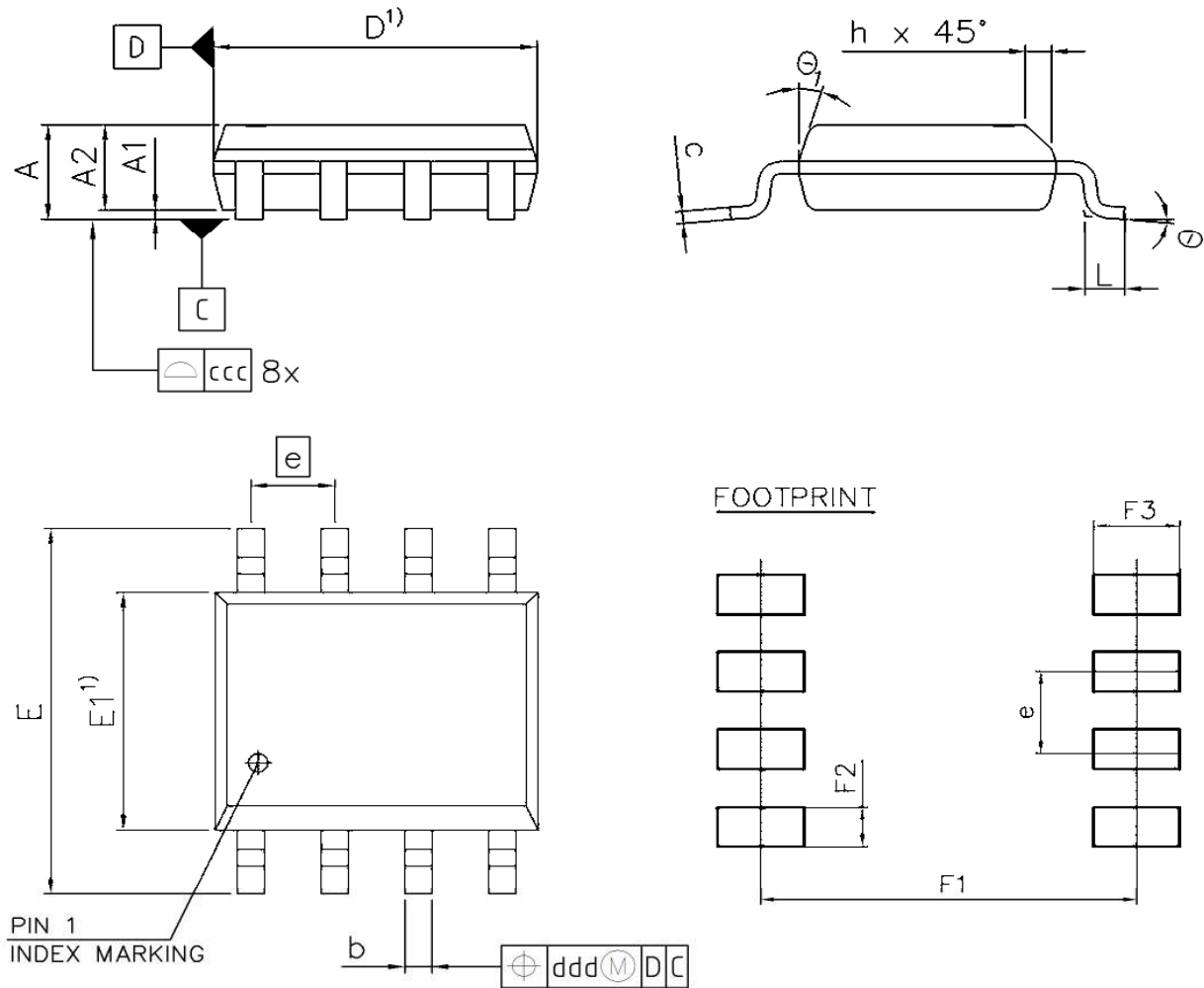


**16 Gate charge waveforms**



Package Outline

PG-DSO-8: Outline



1) DOES NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.75	-	0.069
A1	0.10	-	0.004	-
A2	1.25	1.65	0.049	0.065
b	0.35	0.51	0.014	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27		0.050	
N	8		8	
L	0.39	0.89	0.015	0.035
h	0.23	0.50	0.009	0.020
θ	0°	8°	0°	8°
θ <sub>t</sub>	-	19°	-	19°
ccc	0.10		0.004	
ddd	0.25		0.010	
F1	5.59	5.79	0.220	0.228
F2	0.55	0.75	0.022	0.030
F3	1.21	1.41	0.048	0.056

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- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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